

Amendments to the Specification

Please amend the paragraph beginning at page 5, line 2 as follows:

--In one aspect of the invention there is provided a layered structure including a fullerene layer exhibiting Ohmic behavior. The layered device includes a first layer ~~comprising~~ consisting essentially of fullerenes having a first surface and a second surface opposed to the first surface. The layered structure includes a second layer of pre-selected thickness comprising a fluoride compound located on the first surface of the first layer. The layered structure includes a third layer comprising an electrically conductive material located on the second layer. The pre-selected thickness of the second layer is selected so that the layered structure exhibits substantially Ohmic behavior across the first, second and third layers.--

Please amend the paragraph beginning at page 5, line 12 as follows:

--In another aspect of the present invention there is provided a layered structure including a fullerene layer exhibiting Ohmic behavior. The layered structure includes a first layer ~~comprising~~ consisting essentially of fullerenes having a first surface and a second surface opposed to the first surface. The layered structure includes a second layer comprising a low work function material located on the first surface of the first layer ~~comprising~~ consisting essentially of fullerenes. The layered structure includes a third layer comprising an electrically conductive material located on the second layer. The low work function material is chosen on the basis that the layered structure exhibits substantially Ohmic behavior across the first, second and third layers.--

Please amend the paragraph beginning at page 5, line 21 as follows:

-- In another aspect of the invention there is provided a light-emitting device, comprising a substrate and a first electrically conductive layer forming an anode electrode layer on the substrate. The device includes a hole transport layer on said anode electrode layer, a layer of a light emissive material on said hole transport layer, an electron transport layer comprising fullerenes located on said layer of a light emissive material, and a second electrically conductive layer forming a cathode electrode layer on the electron transport layer. The device includes a layer comprising a light-emissive material interposed between the anode electrode layer and the electron transport layer ~~a first interfacial layer located between said layer of light emissive material and said electron transport material for improving electrical contact between said layer of light emissive material and said layer of electron transport material and a second interfacial layer located between said electron transport layer and said second electrically conductive layer, said interfacial layer comprising a fluoride compound for providing an Ohmic contact between said cathode electrode layer and said fullerene layer.~~

Please amend the paragraph beginning at page 6, line 9 as follows:

In this aspect of the invention the device may include an interfacial layer interposed between the layer consisting essentially of a fullerene and the electrically conductive layer defining a cathode electrode with the material of the interfacial layer being selected so that the interfacial layer makes Ohmic contact with the fullerene layer. ~~The interfacial layer may comprise a fluoride compound and may be an alkaline fluoride compound. The fluoride compound may be calcium fluoride (CaF_2).~~ --

Please amend the paragraph beginning at page 6, line 14 as follows:

-- There may also be an ~~In this aspect of the invention, the first interfacial layer may be a lithium fluoride (LiF) layer of thickness from about~~

0.2nm to about 3nm located between the electron transport layer comprising fullerenes and the layer of light-emissive material. --

Please amend the paragraph beginning at page 6, line 17 as follows:

-- There may also be an a ~~The first~~ interfacial layer interposed between the layer comprising a fullerene and the light-emissive layer ~~may be~~ made from a material which blocks holes whereby the hole blocking layer blocks or prevents holes from leaking into the fullerene layer. --

Please add the following new the paragraph immediately after the paragraph ending at page 6, line 20:

--In another aspect of the present invention there is provided a layered structure including a fullerene layer exhibiting Ohmic behavior, comprising:

a) a first layer consisting essentially of one of a mixture of fullerenes and inorganic materials, and polymeric fullerenes, said first layer having a first surface and a second surface opposed to the first surface;

b) a second layer of pre-selected thickness comprising a fluoride compound located on said first surface of said first layer; and

c) a third layer comprising an electrically conductive material located on the second layer, the pre-selected thickness of the second layer being selected so that the layered structure exhibits substantially Ohmic behavior across the first, second and third layers.--

Please add the following new the paragraph immediately after the above-mentioned new paragraph:

--In another aspect of the present invention there is provided a layered structure including a fullerene layer exhibiting Ohmic behavior, comprising:

a) a first layer consisting essentially of one of a mixture of fullerenes and inorganic materials, and polymeric fullerenes, said first layer having a first surface and a second surface opposed to the first surface;

b) a second layer comprising a low work function material located on said first surface of said first layer; and

c) a third layer comprising an electrically conductive material located on the second layer, the low work function material being selected so that the layered structure exhibits substantially Ohmic behavior across the first, second and third layers.--